

查询UES804供应商

RECTIFIERS

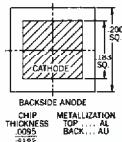
High Efficiency, 50A

捷多邦，专业PCB打样工厂，24小时加急出货

UES804
UES805
UES806
UES804HR2
UES805HR2
UES806HR2

FEATURES

- Very Low Forward Voltage (1.15V)
- Very Fast Recovery Times (50nSec)
- High Surge Capability
- Low Thermal Resistance
- Mechanically Rugged
- Both Polarities Available



ABSOLUTE MAXIMUM RATINGS

Peak Inverse Voltage, UES804, UES804HR2	200V
Peak Inverse Voltage, UES805, UES805HR2	300V
Peak Inverse Voltage, UES806, UES806HR2	400V
Maximum Average D.C. Output Current @ $T_c = 100^\circ\text{C}$	50A
Surge Current, 8.3mS	600A
Thermal Resistance, Junction to Case	.8°C/W
Operating and Storage Temperature Range	-55°C to +150°C

POWER CYCLING

These devices possess the unique ability to pass many thousands of cycles of a stress test designed to evaluate the integrity of the bonding systems used in the construction of power rectifiers.

In this stress test, the case of the device is not heat sunk. Full rated forward current is supplied to force a case temperature increase at least 75°C, at which time, the current is removed and the case allowed to cool. The cycle is repeated a minimum of 5,000 times to simulate equipment being turned on and off. Extended power cycling tests demonstrate a product capability in excess of 25,000 cycles.

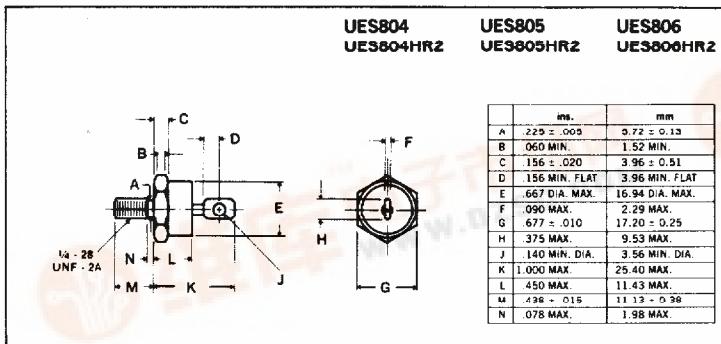
DESCRIPTION

The UES804 is specifically designed for operation in power switching circuits operating at frequencies of at least 20 KHz.

SWITCHING CHARACTERISTICS

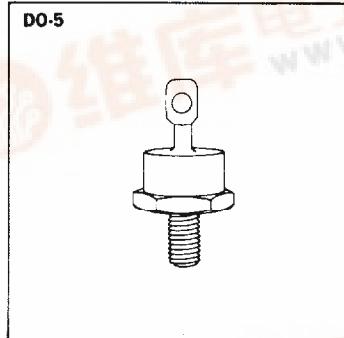
The switching times of these ultra-fast rectifiers increase relatively little, with temperature or at different currents. Even in severe applications, such as catch diodes for switching regulators and output rectifiers for high frequency square wave inverters, these devices switch many times faster than the fastest associated transistors. Thus, the stresses on and powers dissipated in the switching transistors are substantially less than when using other rectifiers.

MECHANICAL SPECIFICATIONS



Notes:

1. Standard polarity is cathode-to-stud.
For reverse polarity (anode-to-stud) add suffix "R", ie. UES804R.
2. All metal surfaces tin plated.
3. Maximum unlubricated stud torque: 30 inch pounds.
4. Angular orientation of terminal is undefined.

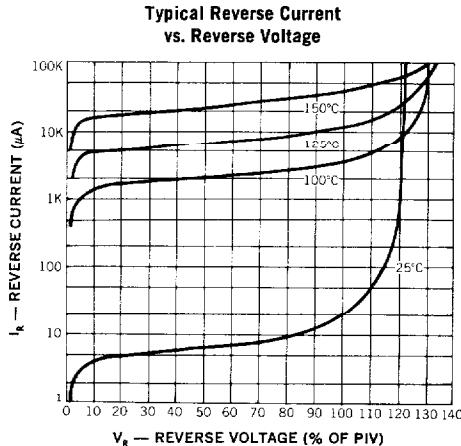
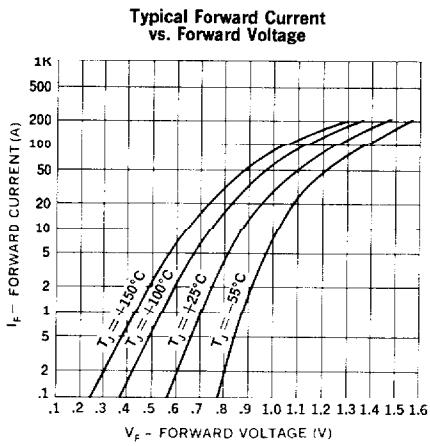
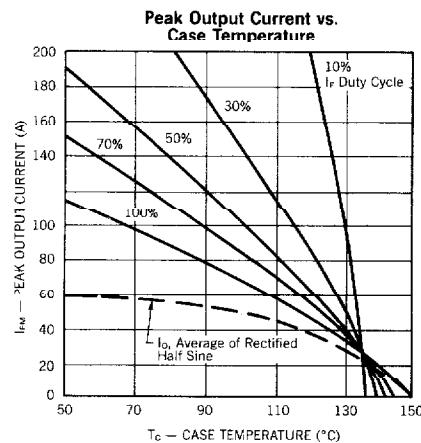
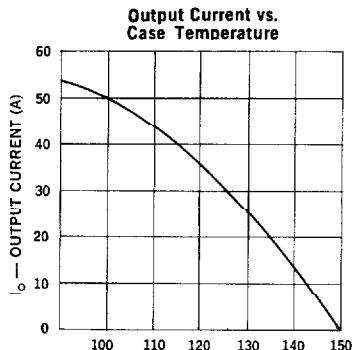


Microsemi Corp.
Watertown
The diode experts

ELECTRICAL SPECIFICATIONS

Type	PIV	maximum Forward Voltage		Maximum Reverse Current		Maximum Reverse Recovery Time*
		$T_c = 25^\circ\text{C}$	$T_c = 125^\circ\text{C}$	$T_c = 25^\circ\text{C}$	$T_c = 125^\circ\text{C}$	
UES804/804HR2	200V	1.25V	@ $I_F = 50\text{A}$	1.15V	@ $I_F = 50\text{A}$	
UES805/805HR2	300V	$t_p = 300\mu\text{s}$		$t_p = 300\mu\text{s}$		
UES806/806HR2	400V					

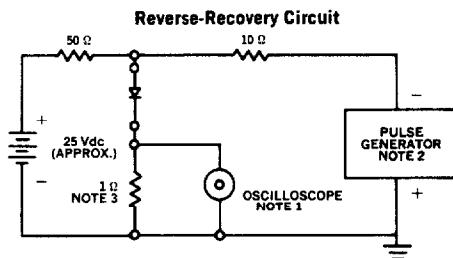
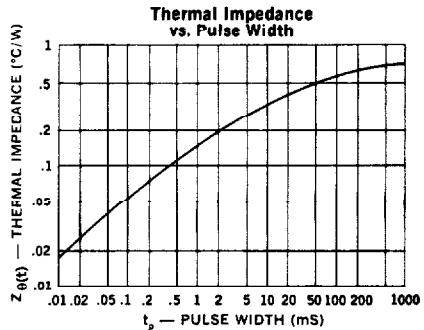
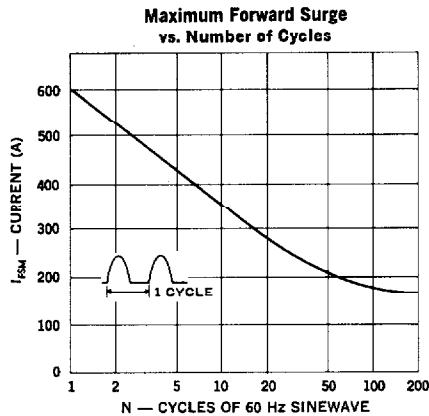
* Measured in circuit $I_F = 0.5\text{A}$, $I_R = 1\text{A}$, $I_{REC} = 0.25\text{A}$



UFS804
UES804HR2

UFS805
UES805HR2

UFS806
UES806HR2



NOTES:

1. Oscilloscope: Rise time $\leq 3\text{ns}$; input impedance = 50Ω .
2. Pulse Generator: Rise time $\leq 8\text{ns}$; source impedance 100Ω .
3. Current viewing resistor, non-inductive, coaxial recommended.

OPTIONAL HIGH RELIABILITY (HR2) SCREENING

The following tests are performed on 100% of the devices specified UES804HR2, 5HR2, 6HR2.

SCREEN	MIL-STD-750 METHOD	CONDITIONS
1. High Temperature	1032	24 Hours @ $T_A = 150^\circ\text{C}$
2. Temperature Cycle	1051	F, 20 Cycles, -55 to $+150^\circ\text{C}$. No dwell required @ 25°C , $t \geq 10\text{ min}$. @ extremes
3. Hermetic Seal a. Fine Leak b. Gross Leak	1071	H, Helium C, Liquid
4. Thermal Impedance		Sage Test
5. Interim Electrical Parameters	GO/NO GO	V_F and I_R @ 25°C
6. High Temperature Reverse Blocking	Similar to Method 1040	$\frac{1}{2}$ Sine Reverse, $t = 48$ Hours, $T_C = 125^\circ\text{C}$, VRW_M = rating, F = 50-60 Hz, $I_O = 0\text{A}$
7. Final Electrical Parameters	GO/NO GO	$V_F + I_R$ @ 25°C PDA = 10% (Final Electricals)